

1. General description

Planar passivated high commutation three quadrant triac in a SOT223 surface mountable plastic package. This "series ET" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only

3. Applications

- General purpose motor control
- Small loads in washing machines
- Solenoid drivers

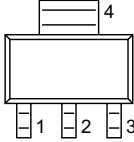
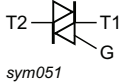
4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Notes | Values | | | Unit |
|--------------------------------|--------------------------------------|---|-------|------------|------|------|------|
| Absolute maximum rating | | | | | | | |
| V_{DRM} | repetitive peak off-state voltage | | | 600 | | | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{sp} \leq 115\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3 | | 2 | | | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5 | | 17 | | | A |
| | | full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$ | | 18.7 | | | A |
| T_j | operating junction temperature | | | -40 to 150 | | | °C |
| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
| Static characteristics | | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 9 | | 1 | - | 10 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 9 | | 1 | - | 10 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 9 | | 1 | - | 10 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 11 | | - | - | 12 | mA |
| V_T | on-state voltage | $I_T = 2.0\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12 | | - | 1.35 | 1.55 | V |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------|--|---|
| 1 | T1 | main terminal 1 |  |  sym051 |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| 4 | T2 | main terminal 2 | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package Name | Orderable part number | Packing method | Small packing quantity | Package version | Package issue date |
|---------------|--------------|-----------------------|----------------|------------------------|-----------------|--------------------|
| BTA302W-600ET | SOT223 | BTA302W-600ETF | Reel | 4000 | SOT223 | 16-Mar-2006 |

7. Marking

Table 4. Marking codes

| Type number | Marking codes | |
|---------------|---------------------|---------------------|
| | Assembly factory: d | Assembly factory: L |
| BTA302W-600ET | Jdxxx 302W6E | JLxxx 302W6E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Notes | Max | Unit |
|--------------|--------------------------------------|--|-------|------------|------------------------|
| V_{DRM} | repetitive peak off-state voltage | | | 600 | V |
| V_{RRM} | repetitive peak reverse voltage | | | 600 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{sp} \leq 115\text{ }^{\circ}\text{C}$; Fig 1 ; Fig 2 ; Fig 3 | | 2 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(imit)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig 4 ; Fig 5 | | 17 | A |
| | | full sine wave; $T_{j(imit)} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$ | | 18.7 | A |
| I^2t | I^2t for fusing | $t_p = 10\text{ ms}$; SIN | | 1.4 | A^2s |
| di_T/dt | rate of rise of on-state current | $I_G = 20\text{ mA}$ | | 100 | $\text{A}/\mu\text{s}$ |
| I_{GM} | peak gate current | | | 2 | A |
| P_{GM} | peak gate power | | | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | | 0.1 | W |
| T_{stg} | storage temperature | | | -40 to 150 | $^{\circ}\text{C}$ |
| T_j | operating junction temperature | | | -40 to 150 | $^{\circ}\text{C}$ |

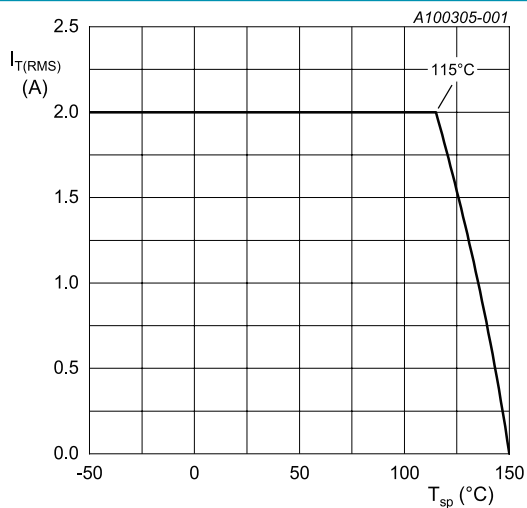
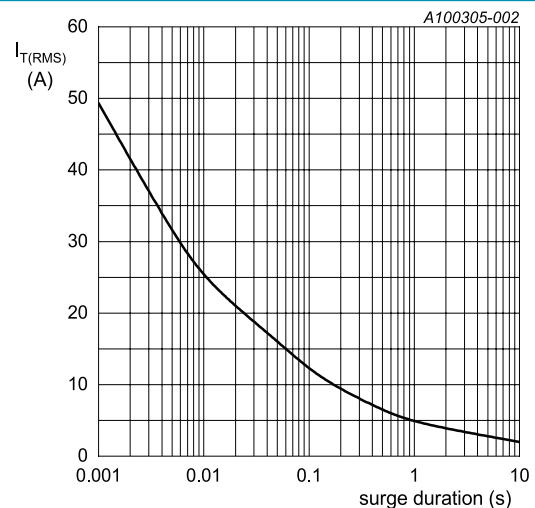


Fig. 1. RMS on-state current as a function of solder point temperature; maximum values



$f = 50\text{ Hz}$; $T_{sp} = 115\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

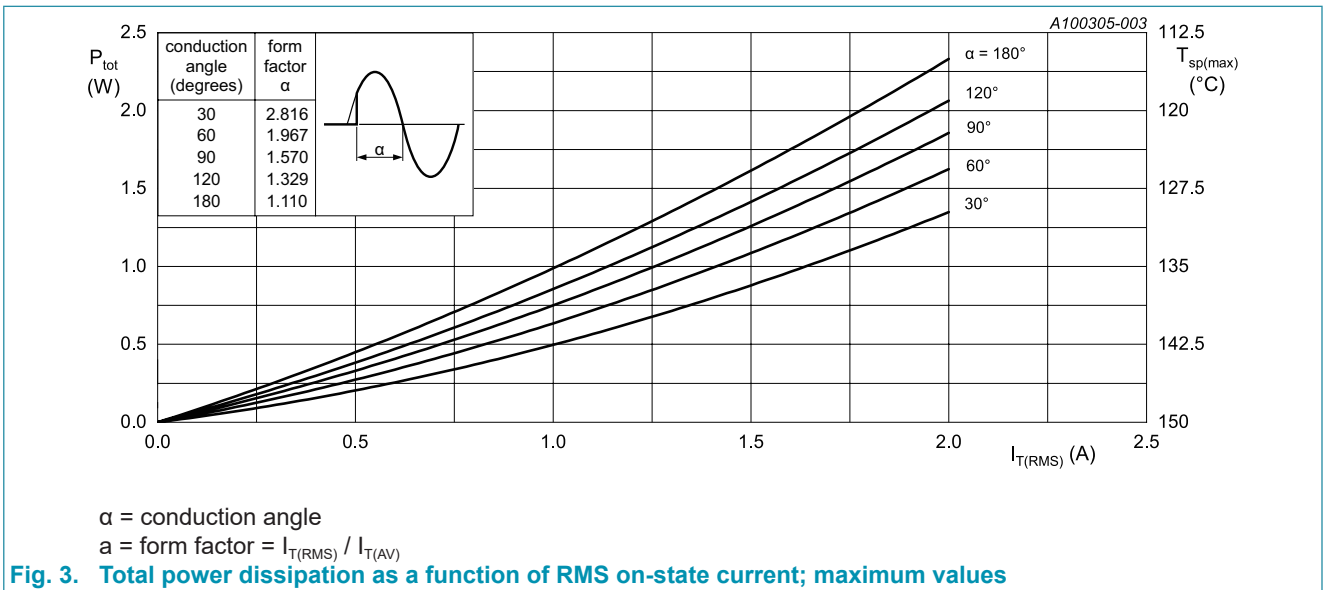


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

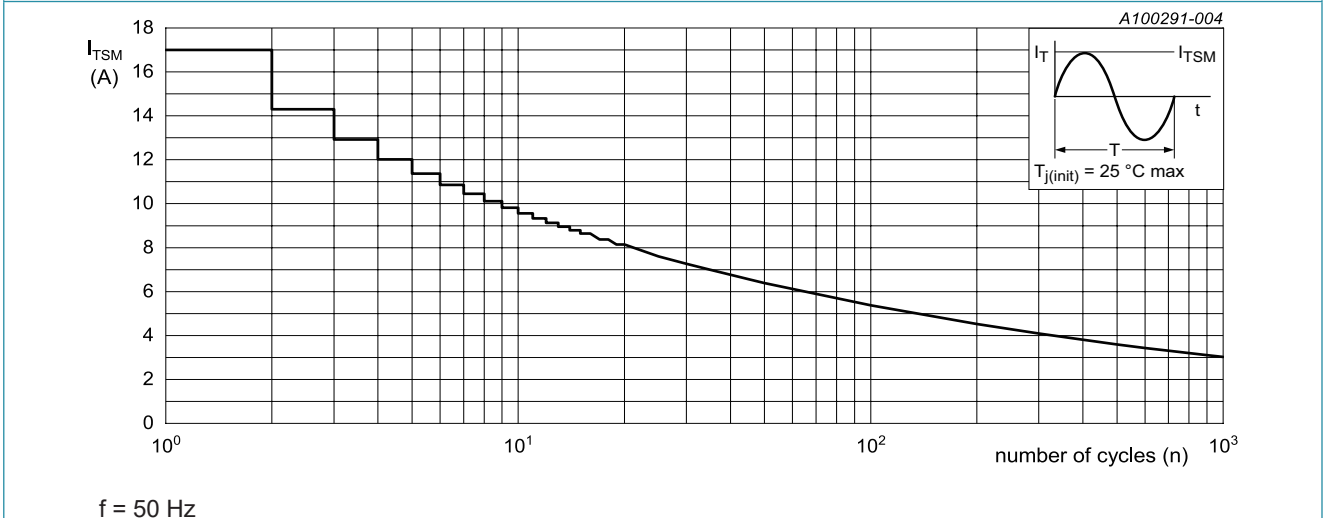


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

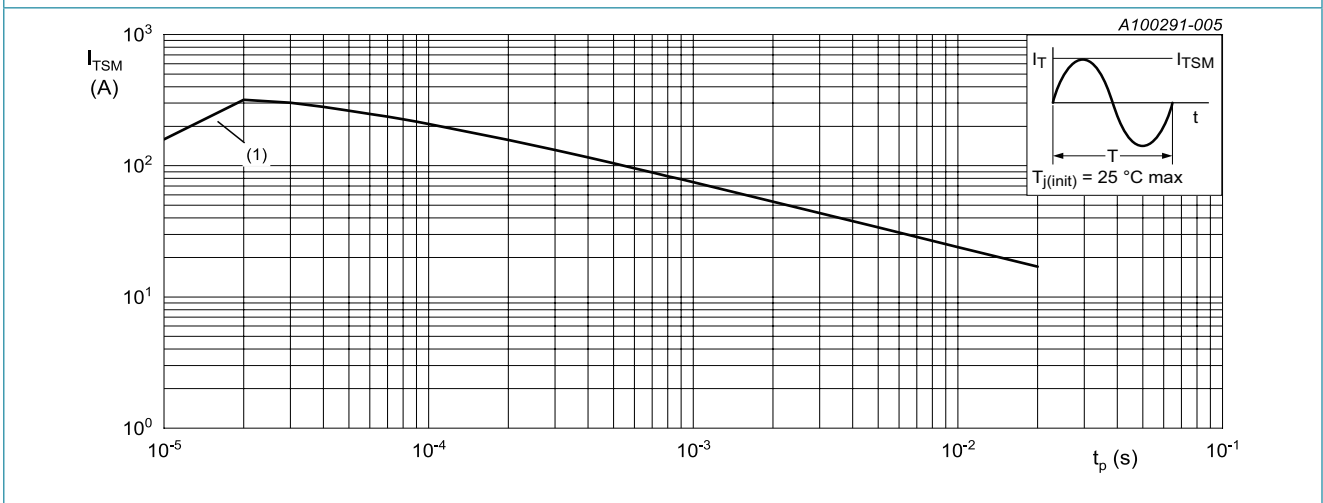


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
|----------------|--|--|-------|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | full cycle; Fig 6 | | - | - | 15 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air; printed-circuit board mounted; minimum footprint; Fig 7 | | - | 156 | - | K/W |
| | | in free air; printed-circuit board mounted; pad area; Fig 8 | | - | 70 | - | K/W |

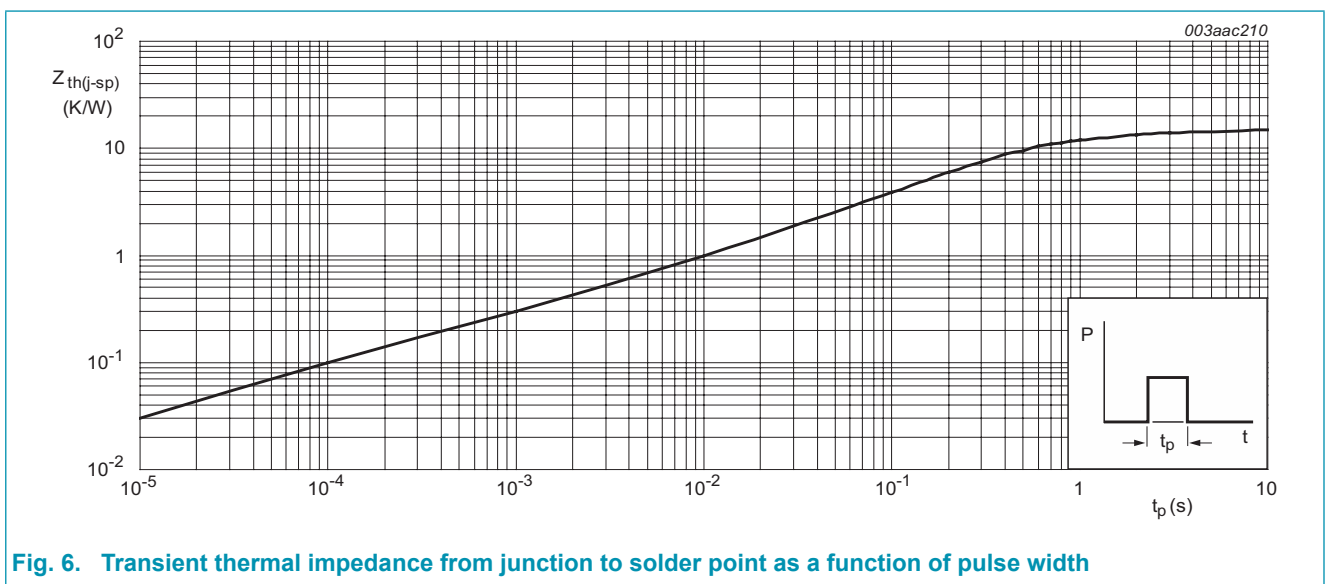
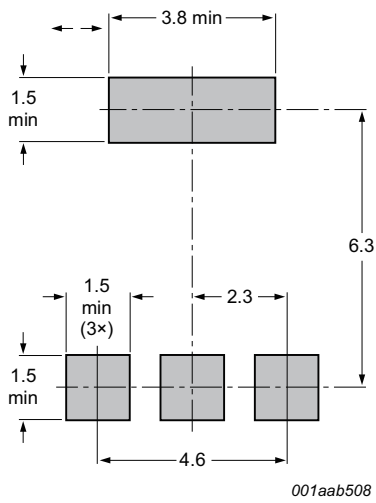
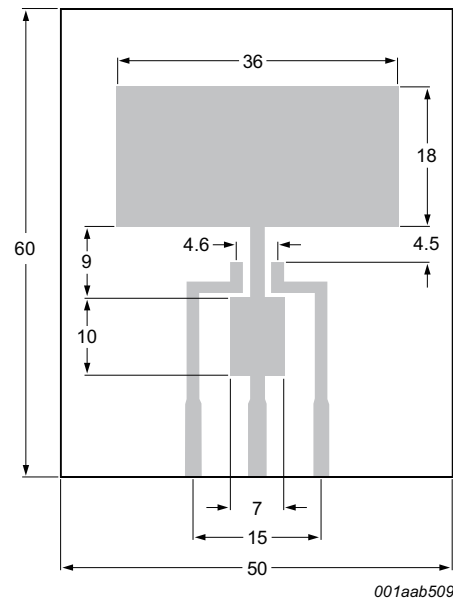


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm

Fig. 7. Minimum footprint SOT223



All dimensions are in mm

Printed circuit board:

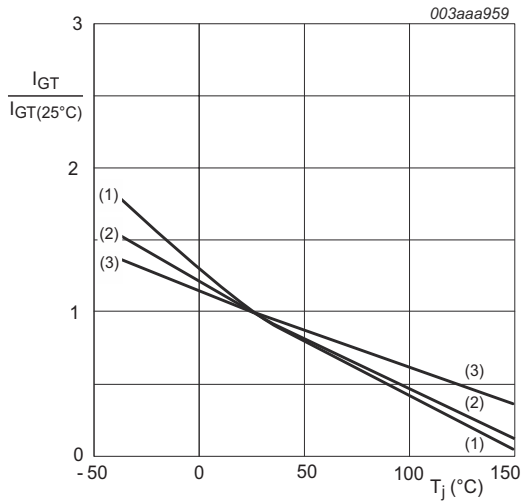
FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

Fig. 8. Printed circuit board pad area: SOT223

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Notes | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-------|-----|------|------|------------|
| Static characteristics | | | | | | | |
| I_{GT} | gate trigger current | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 9 | | 1 | - | 10 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 9 | | 1 | - | 10 | mA |
| | | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 9 | | 1 | - | 10 | mA |
| I_L | latching current | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ °C}$; Fig. 10 | | - | - | 12 | mA |
| | | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ °C}$; Fig. 10 | | - | - | 20 | mA |
| | | $V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ °C}$; Fig. 10 | | - | - | 12 | mA |
| I_H | holding current | $V_D = 12\text{ V}$; $T_J = 25\text{ °C}$; Fig. 11 | | - | - | 12 | mA |
| V_T | on-state voltage | $I_T = 2.0\text{ A}$; $T_J = 25\text{ °C}$; Fig. 12 | | - | 1.35 | 1.55 | V |
| V_{GT} | gate trigger voltage | $V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ °C}$; Fig. 13 | | - | 0.7 | 1 | V |
| | | $V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ °C}$ | | 0.2 | 0.3 | - | V |
| I_D | off-state current | $V_D = 600\text{ V}$; $T_J = 150\text{ °C}$ | | - | - | 2 | mA |
| I_R | reverse current | $V_R = 600\text{ V}$; $T_J = 150\text{ °C}$ | | - | - | 2 | mA |
| Dynamic characteristics | | | | | | | |
| dV_D/dt | rate of rise of off-state voltage | $V_{DM} = 402\text{ V}$; $T_J = 125\text{ °C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit | | 600 | - | - | V/ μ s |
| dI_{com}/dt | rate of change of commutating current | $V_D = 400\text{ V}$; $T_J = 125\text{ °C}$; $I_{T(RMS)} = 1.0\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | | 2.5 | - | - | A/ms |
| | | $V_D = 400\text{ V}$; $T_J = 125\text{ °C}$; $I_{T(RMS)} = 1.0\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit | | 3.5 | - | - | A/ms |



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

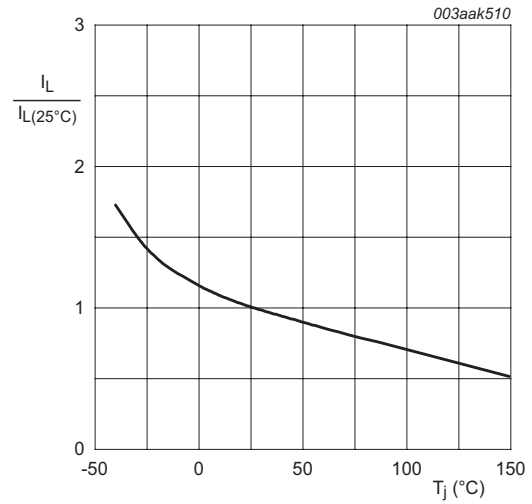


Fig. 10. Normalized latching current as a function of junction temperature

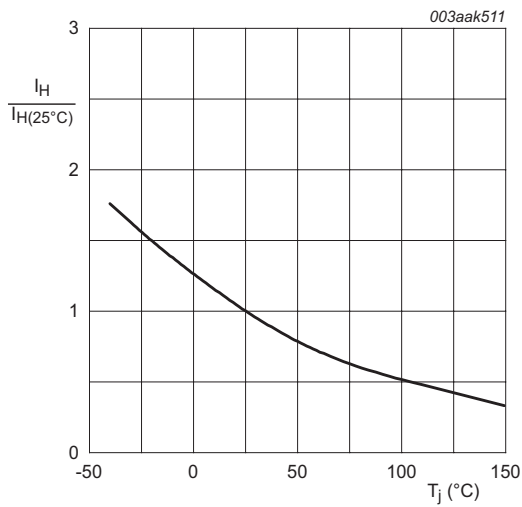
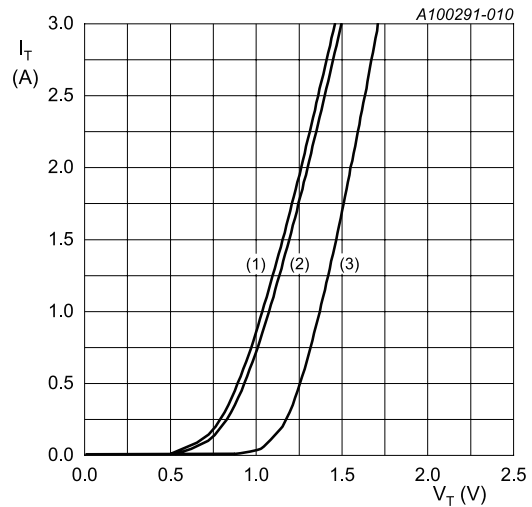


Fig. 11. Normalized holding current as a function of junction temperature



- $V_o = 0.900 \text{ V}; R_s = 0.1775 \Omega$
- (1) $T_j = 150^{\circ}\text{C}$; typical values
 - (2) $T_j = 150^{\circ}\text{C}$; maximum values
 - (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 12. On-state current as a function of on-state voltage

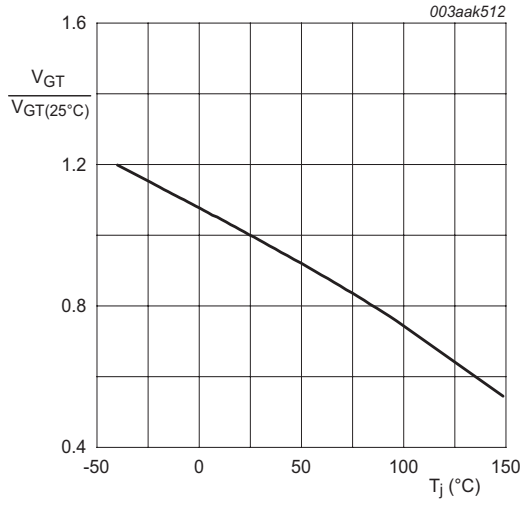
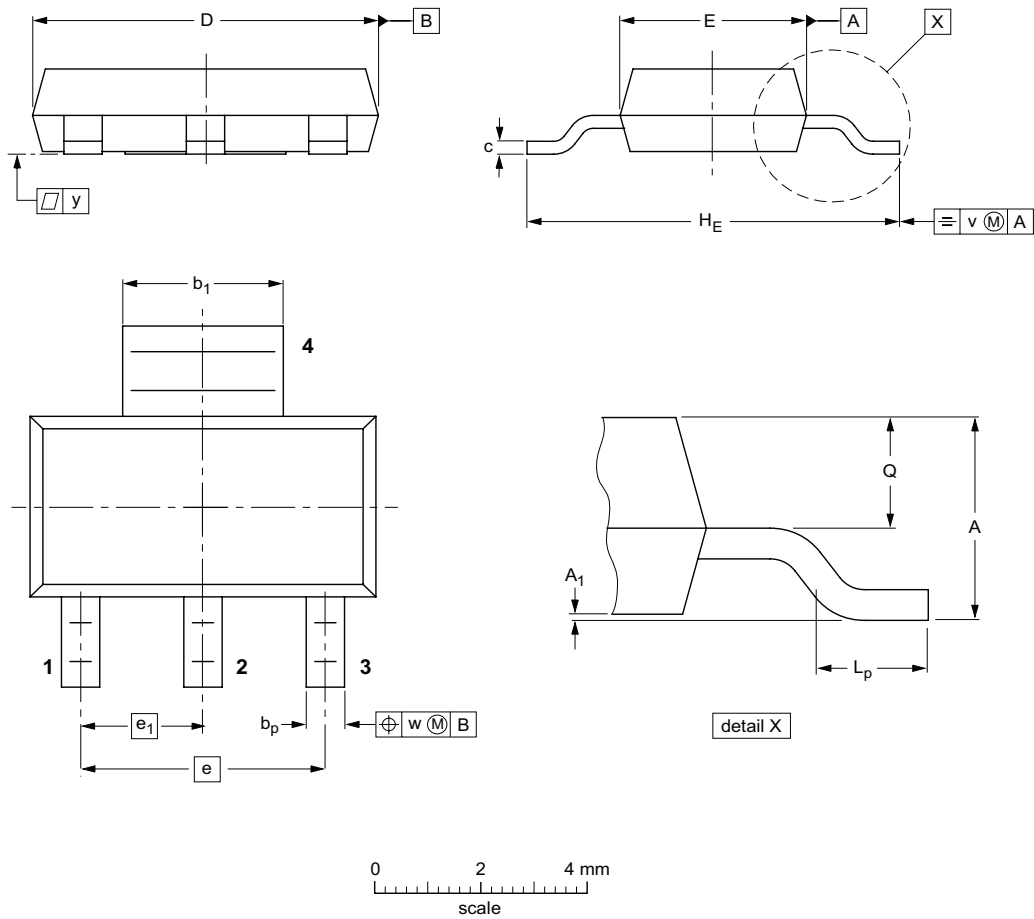


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic surface-mounted package with increased heatsink; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b _p | b ₁ | c | D | E | e | e ₁ | H _E | L _p | Q | v | w | y |
|------|------------|----------------|----------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|--------------|-----|-----|-----|
| mm | 1.8 1.5 | 0.10 0.01 | 0.80 0.60 | 3.1 2.9 | 0.32 0.22 | 6.7 6.3 | 3.7 3.3 | 4.6 | 2.3 | 7.3 6.7 | 1.1 0.7 | 0.95 0.85 | 0.2 | 0.1 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|-------|--|---------------------|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT223 | | | SC-73 | | | 04-11-10 06-03-16 |

12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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